INTEGRATED CIRCUITS

DATA SHEET

74ABT640

Octal transceiver with direction pin, inverting (3-State)

Product specification
Supersedes data of 1993 Jun 21
IC23 Data Handbook

1998 Jan 16





74ABT640

FEATURES

- Octal bidirectional bus interface
- 3-State buffers
- Power-up 3-State
- Live insertion/extraction permitted
- Output capability: +64mA/-32mA
- Latch-up protection exceeds 500mA per Jedec Std 17
- ESD protection exceeds 2000 V per MIL STD 883 Method 3015 and 200 V per Machine Model

DESCRIPTION

The 74ABT640 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT640 device is an octal transceiver featuring inverting 3-State bus compatible outputs in both send and receive directions. The control function implementation minimizes external timing requirements. The device features an Output Enable (\overline{OE}) input for easy cascading and a Direction (DIR) input for direction control.

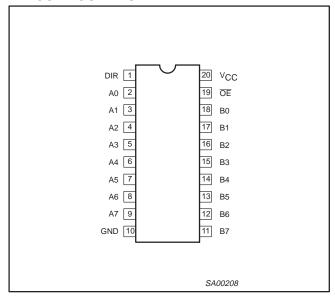
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS T _{amb} = 25°C; GND = 0V	TYPICAL	UNIT
t _{PLH} t _{PHL}	Propagation delay An to Bn or Bn to An	$C_L = 50pF; V_{CC} = 5V$	3.1	ns
C _{IN}	Input capacitance DIR, OE	$V_I = 0V$ or V_{CC}	4	pF
C _{I/O}	I/O capacitance	Outputs disabled; V _O = 0V or V _{CC}	7	pF
I _{CCZ}	Total supply current	Outputs disabled; V _{CC} =5.5V	50	μΑ

ORDERING INFORMATION

<u> </u>				
PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
20-Pin Plastic DIP	-40°C to +85°C	74ABT640 N	74ABT640 N	SOT146-1
20-Pin plastic SO	-40°C to +85°C	74ABT640 D	74ABT640 D	SOT163-1
20-Pin Plastic SSOP Type II	-40°C to +85°C	74ABT640 DB	74ABT640 DB	SOT339-1
20-Pin Plastic TSSOP Type I	-40°C to +85°C	74ABT640 PW	74ABT640PW DH	SOT360-1

PIN CONFIGURATION



PIN DESCRIPTION

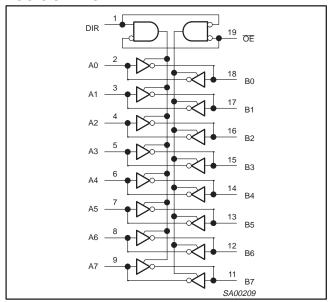
PIN NUMBER	SYMBOL	NAME AND FUNCTION
1	DIR	Direction control input
2, 3, 4, 5, 6, 7, 8, 9	A0 – A7	Data inputs/outputs (A side)
18, 17, 16, 15, 14, 13, 12, 11	B0 – B7	Data inputs/outputs (B side)
19	ŌĒ	Output enable input, B side to A side (active-Low)
10	GND	Ground (0V)
20	V _{CC}	Positive supply voltage

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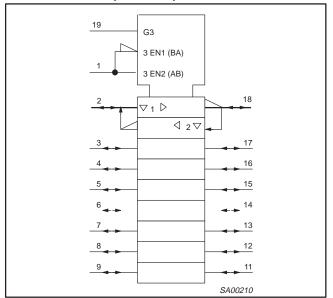
Octal transceiver with direction pin, inverting (3-State)

74ABT640

LOGIC SYMBOL



LOGIC SYMBOL (IEEE/IEC)



FUNCTION TABLE

INP	UTS	INPUTS/OUTPUTS					
ŌĒ	DIR	An	Bn				
L	L	Bn	Inputs				
L	Н	Inputs	Ān				
Н	Х	Z	Z				

- H = High voltage level
- L = Low voltage level
- X = Don't care
- Z = High impedance "off" state

ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
I _{IK}	DC input diode current	V _I < 0	-18	mA
VI	DC input voltage ³		-1.2 to +7.0	V
lok	DC output diode current	V _O < 0	-50	mA
V _{OUT}	DC output voltage ³	output in Off or High state	-0.5 to +5.5	V
I _{OUT}	DC output current	output in Low state	128	mA
T _{stg}	Storage temperature range		-65 to 150	°C

NOTES:

- 1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- 2. The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.

3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIM	ITS	UNIT
		Min	Max	
V _{CC}	DC supply voltage	4.5	5.5	V
VI	Input voltage	0	V _{CC}	V
V _{IH}	High-level input voltage	2.0		V
V _{IL}	Low-level input voltage		0.8	V
I _{OH}	High-level output current		-32	mA
I _{OL}	Low-level output current		64	mA
Δt/Δν	Input transition rise or fall rate	0	5	ns/V
T _{amb}	Operating free-air temperature range	-40	+85	°C

DC ELECTRICAL CHARACTERISTICS

						LIMITS			
SYMBOL	PARAM	ETER	TEST CONDITIONS	Tai	_{mb} = +25	s∘ C	T _{amb} =	–40°C 85°C	UNIT
				Min	Тур	Max	Min	Max	
V _{IK}	Input clamp voltage		V _{CC} = 4.5V; I _{IK} = -18mA		-0.9	-1.2		-1.2	V
			$V_{CC} = 4.5V$; $I_{OH} = -3mA$; $V_I = V_{IL}$ or V_{IH}	2.5	2.9		2.5		V
V _{OH}	High-level outpu	ut voltage	$V_{CC} = 5.0V$; $I_{OH} = -3mA$; $V_I = V_{IL}$ or V_{IH}	3.0	3.4		3.0		V
			$V_{CC} = 4.5V$; $I_{OH} = -32mA$; $V_I = V_{IL}$ or V_{IH}	2.0	2.4		2.0		V
V _{OL}	Low-level output voltage		$V_{CC} = 4.5V$; $I_{OL} = 64mA$; $V_I = V_{IL}$ or V_{IH}		0.42	0.55		0.55	V
I _I	Input leakage	Control pins	V _{CC} = 5.5V; V _I = GND or 5.5V		±0.01	±1.0		±1.0	μΑ
	current Data pins		$V_{CC} = 5.5V; V_I = GND \text{ or } 5.5V$		±5	±100		±100	μΑ
I _{OFF}	Power-off leakage current		$V_{CC} = 0.0V$; V_I or $V_O \le 4.5V$		±5.0	±100		±100	μΑ
I _{PU} /I _{PD}	Power-up/down output current ³	3-State	V_{CC} = 2.1V; V_{O} = 0.5V; V_{I} = GND or V_{CC} ; V_{OE} = Don't care		±5.0	±50		±50	μА
I _{IH} + I _{OZH}	3-State output H	ligh current	$V_{CC} = 5.5V; V_O = 2.7V; V_I = V_{IL} \text{ or } V_{IH}$		5.0	50		50	μΑ
I _{IL} + I _{OZL}	3-State output L	ow current	$V_{CC} = 5.5V; V_O = 0.5V; V_I = V_{IL} \text{ or } V_{IH}$		-5.0	-50		-50	μΑ
I _{CEX}	Output High lea	kage current	V_{CC} = 5.5V; V_{O} = 5.5V; V_{I} = GND or V_{CC}		5.0	50		50	μΑ
Io	Output current ¹		$V_{CC} = 5.5V; V_{O} = 2.5V$	-50	-100	-180	-50	-180	mA
Іссн			V_{CC} = 5.5V; Outputs High, V_I = GND or V_{CC}		50	250		250	μΑ
I _{CCL}	Quiescent supp	ly current	V_{CC} = 5.5V; Outputs Low, V_I = GND or V_{CC}		24	30		30	mA
I _{CCZ}			V_{CC} = 5.5V; Outputs 3-State; V_I = GND or V_{CC}		50	250		250	μΑ
Δl _{CC}	Additional suppingular pin ²	ly current per	$V_{\rm CC}$ = 5.5V; one input at 3.4V, other inputs at $V_{\rm CC}$ or GND		0.05	1.5		1.5	mA

- 1. Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
- This is the increase in supply current for each input at 3.4V.
 This parameter is valid for any V_{CC} between 0V and 2.1V, with a transition time of up to 10msec. From V_{CC} = 2.1V to V_{CC} = 5V ±10% a transition time of up to 100µsec is permitted.

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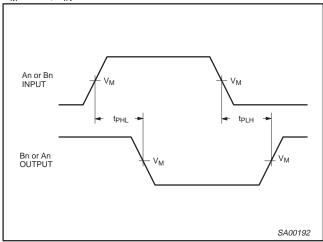
AC CHARACTERISTICS

GND = 0V; t_R = t_F = 2.5ns; C_L = 50pF, R_L = 500 Ω

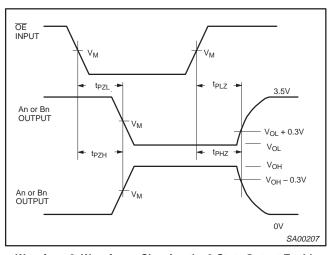
SYMBOL	PARAMETER	WAVEFORM	T _a	_{amb} = +25° ' _{CC} = +5.0'	C V	T _{amb} = -40° V _{CC} = +5.	UNIT	
			Min	Тур	Max	Min	Max	
t _{PLH} t _{PHL}	Propagation delay An to Bn or Bn to An	1	1.0 1.5	2.8 3.1	4.2 4.3	1.0 1.5	4.9 4.9	ns
t _{PZH} t _{PZL}	Output enable time to High and Low level	2	1.5 1.3	3.6 3.2	4.9 5.9	1.5 1.3	5.8 7.3	ns
t _{PHZ}	Output disable time from High and Low Level	2	2.5 2.0	5.2 4.1	6.5 5.3	2.5 2.0	6.8 5.5	ns

AC WAVEFORMS

 $V_{M} = 1.5V, V_{IN} = GND \text{ to } 3.0V$

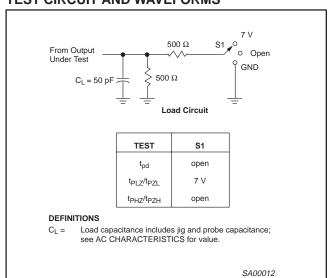


Waveform 1. Waveforms Showing the Input to Output Propagation Delays



Waveform 2. Waveforms Showing the 3-State Output Enable and Disable Times

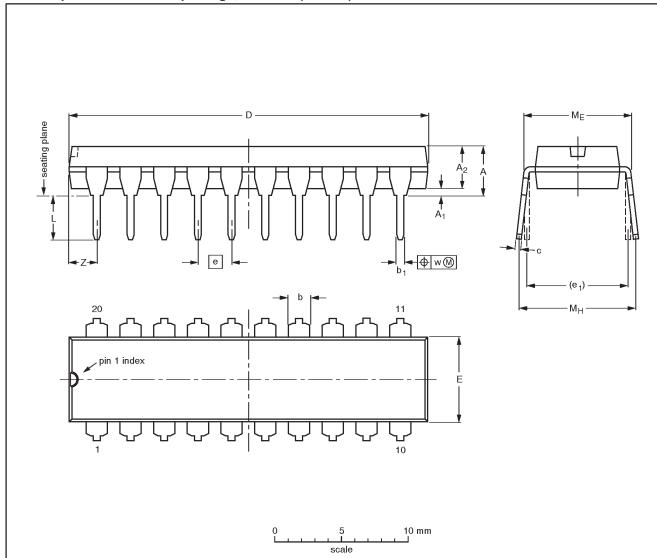
TEST CIRCUIT AND WAVEFORMS



74ABT640

DIP20: plastic dual in-line package; 20 leads (300 mil)

SOT146-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	0.36 0.23	26.92 26.54	6.40 6.22	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.0
inches	0.17	0.020	0.13	0.068 0.051	0.021 0.015	0.014 0.009	1.060 1.045	0.25 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.078

Note

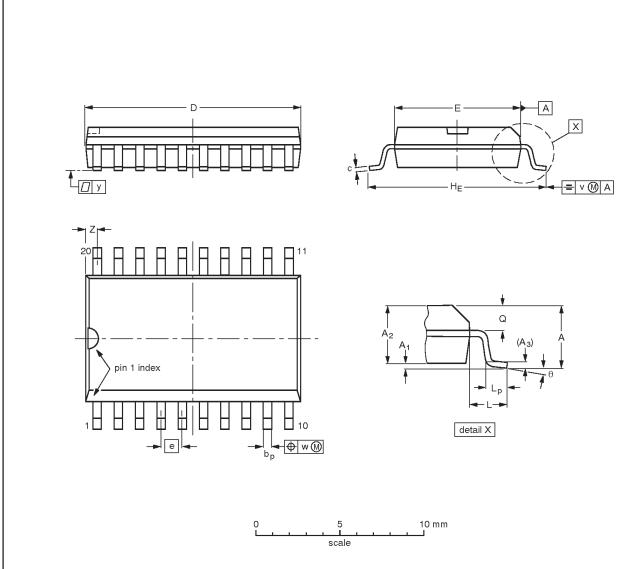
1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT146-1			SC603		92-11-17 95-05-24

74ABT640

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	bp	O	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	z ⁽¹⁾	θ
mm	2.65	0.30 0.10	2.45 2.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8°
inches	0.10	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.050	0.42 0.39	0.055		0.043 0.039	0.01	0.01	0.004	0.035 0.016	o°

Note

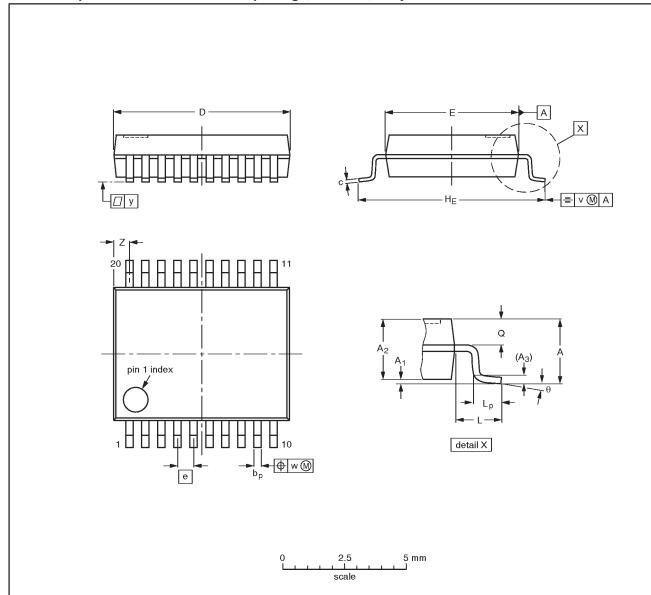
1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	1330E DATE
SOT163-1	075E04	MS-013AC			-92-11-17 95-01-24

74ABT640

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	Α1	A ₂	A ₃	bр	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Ø	v	w	у	Z ⁽¹⁾	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	7.4 7.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	0.9 0.5	8° 0°

Note

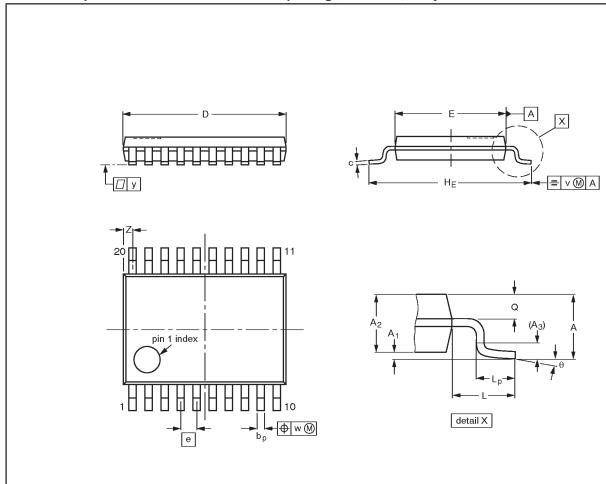
1. Plastic or metal protrusions of 0.20 mm maximum per side are not included.

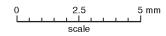
OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT339-1		MO-150AE			93-09-08 95-02-04

74ABT640

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1





DIMENSIONS (mm are the original dimensions)

UNIT	A max.	Α1	A ₂	A ₃	рb	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Œ	v	w	у	Z ⁽¹⁾	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	RENCES	EUROPEAN	ICCUE DATE	
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE	
SOT360-1		MO-153AC			-93-06-16 95-02-04	

Philips Semiconductors Product specification

Octal transceiver with direction pin, inverting (3-State)

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Data sheet status

Data sheet status	Product status	Definition [1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make chages at any time without notice in order to improve design and supply the best possible product.
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^[1] Please consult the most recently issued datasheet before initiating or completing a design.

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